

STARPOWER

SEMICONDUCTOR

IGBT

GD450HFL170C6S

1700V/450A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

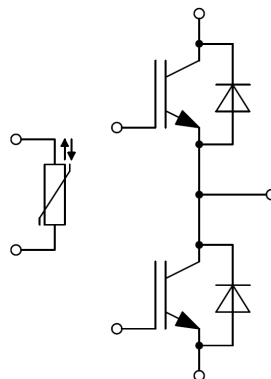
- Low $V_{CE(sat)}$ SPT+ IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1700	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	760	A
	@ $T_C=100^{\circ}\text{C}$	450	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	900	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	3261	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1700	V
I_F	Diode Continuous Forward Current	450	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	900	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=450\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.00	2.45	V	
		$I_C=450\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.40			
		$I_C=450\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.50			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=18.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.4	6.2	7.4	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		30.0		nF	
C_{res}	Reverse Transfer Capacitance				1.08		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		2.70		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=450\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		504		ns	
t_r	Rise Time				183		ns
$t_{d(off)}$	Turn-Off Delay Time				616		ns
t_f	Fall Time				188		ns
E_{on}	Turn-On Switching Loss				126		mJ
E_{off}	Turn-Off Switching Loss				88.8		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=450\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		506		ns	
t_r	Rise Time				194		ns
$t_{d(off)}$	Turn-Off Delay Time				704		ns
t_f	Fall Time				352		ns
E_{on}	Turn-On Switching Loss				162		mJ
E_{off}	Turn-Off Switching Loss				124		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=450\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		510		ns	
t_r	Rise Time				198		ns
$t_{d(off)}$	Turn-Off Delay Time				727		ns
t_f	Fall Time				429		ns
E_{on}	Turn-On Switching Loss				174		mJ
E_{off}	Turn-Off Switching Loss				132		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=1000\text{V}, V_{CEM} \leq 1700\text{V}$		1440		A	

Diode Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=450\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.80	2.25	V
		$I_F=450\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.95		
		$I_F=450\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.90		
Q_r	Recovered Charge			111		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=900\text{V}, I_F=450\text{A},$ $-di/dt=2350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		345		A
E_{rec}	Reverse Recovery Energy			64.6		mJ
Q_r	Recovered Charge			161		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=900\text{V}, I_F=450\text{A},$ $-di/dt=2350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		392		A
E_{rec}	Reverse Recovery Energy			95.1		mJ
Q_r	Recovered Charge			177		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=900\text{V}, I_F=450\text{A},$ $-di/dt=2350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		408		A
E_{rec}	Reverse Recovery Energy			104		mJ

NTC Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_c=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Module Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		1.10		$\text{m}\Omega$
$R_{\theta JC}$	Junction-to-Case (per IGBT)			0.046	K/W
	Junction-to-Case (per Diode)			0.080	
$R_{\theta CS}$	Case-to-Sink (per IGBT)		0.028		K/W
	Case-to-Sink (per Diode)		0.049		
$R_{\theta CS}$	Case-to-Sink		0.009		K/W
M	Terminal Connection Torque, Screw M6	3.0		6.0	N.m
	Mounting Torque, Screw M5	3.0		6.0	
G	Weight of Module		350		g

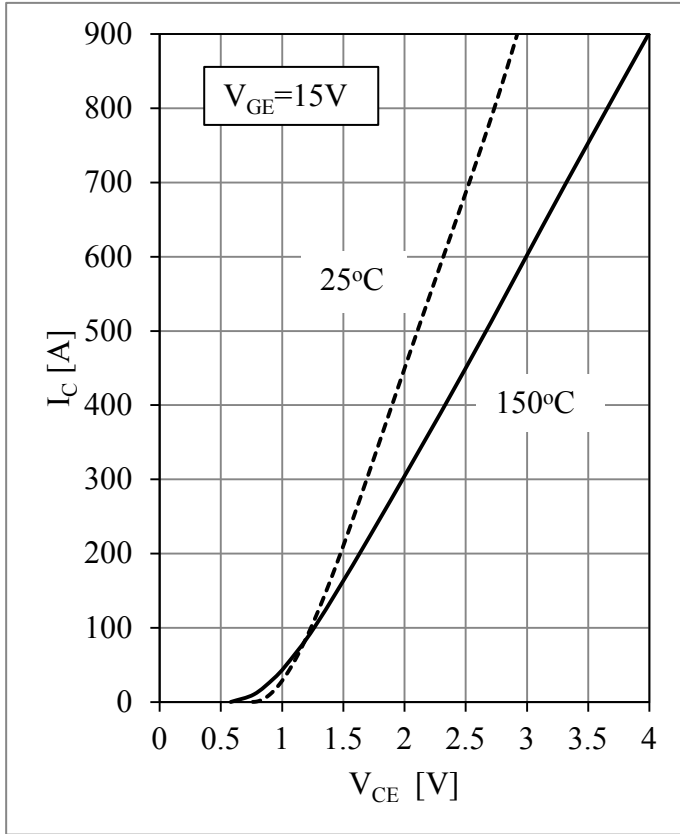


Fig 1. IGBT Output Characteristics

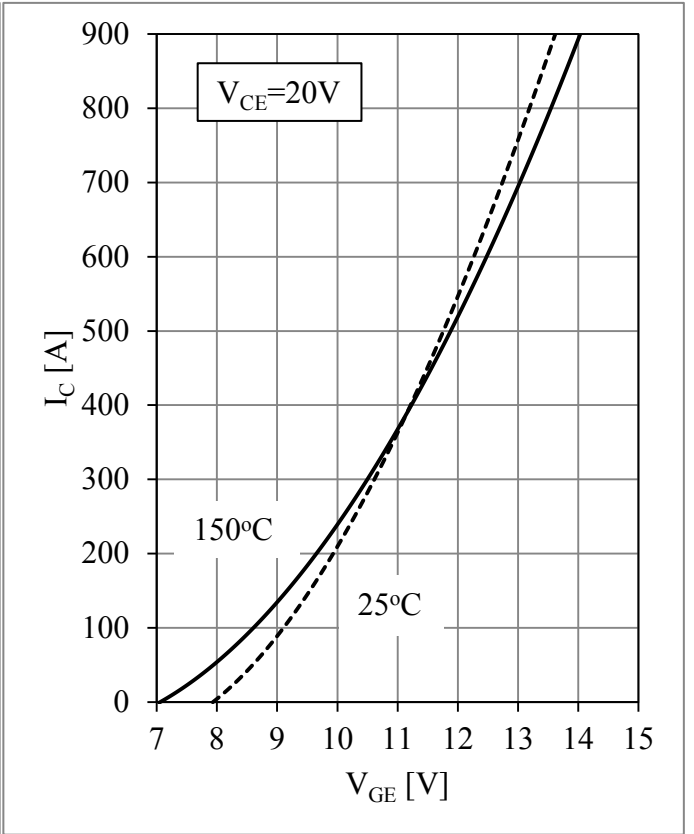


Fig 2. IGBT Transfer Characteristics

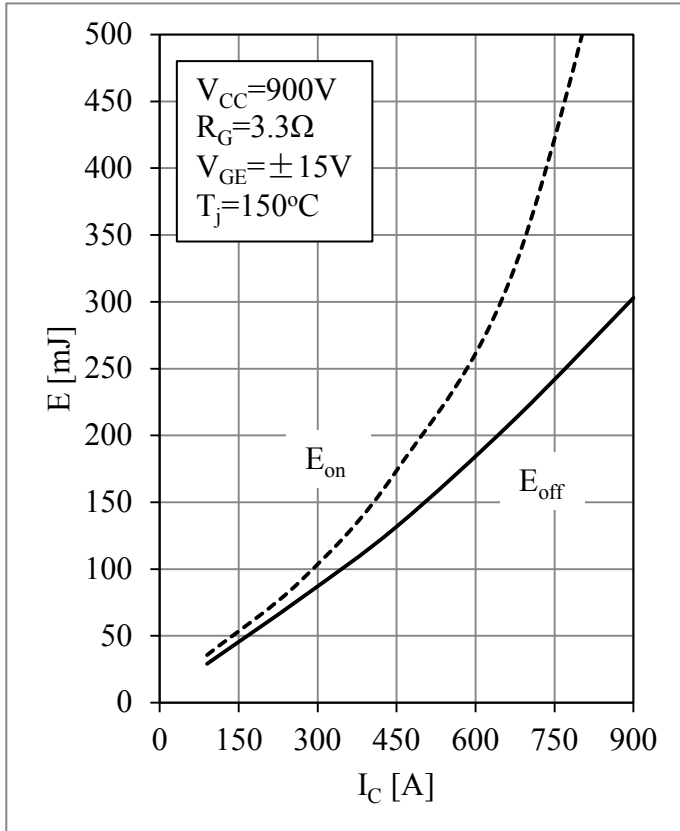


Fig 3. IGBT Switching Loss vs. I_C

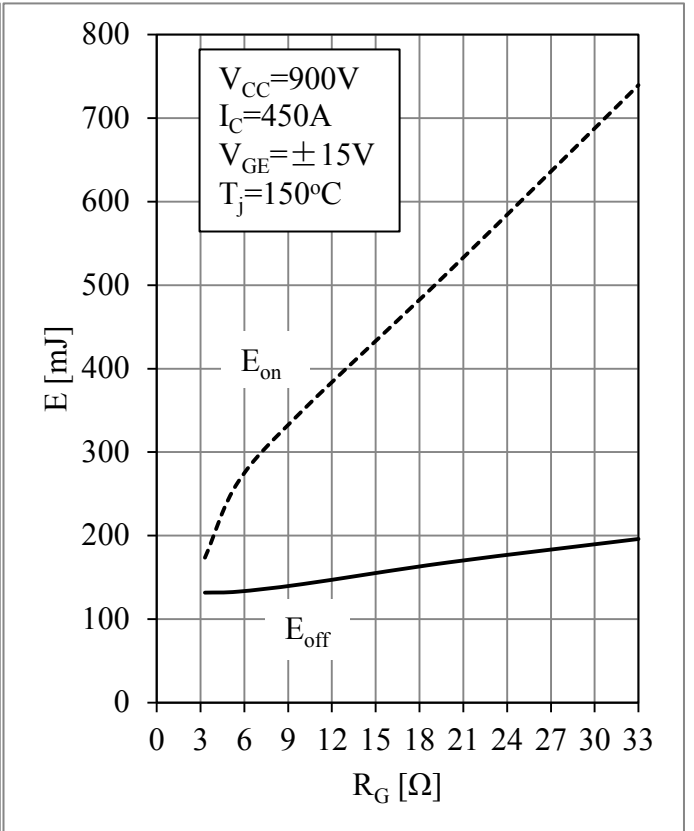


Fig 4. IGBT Switching Loss vs. R_G

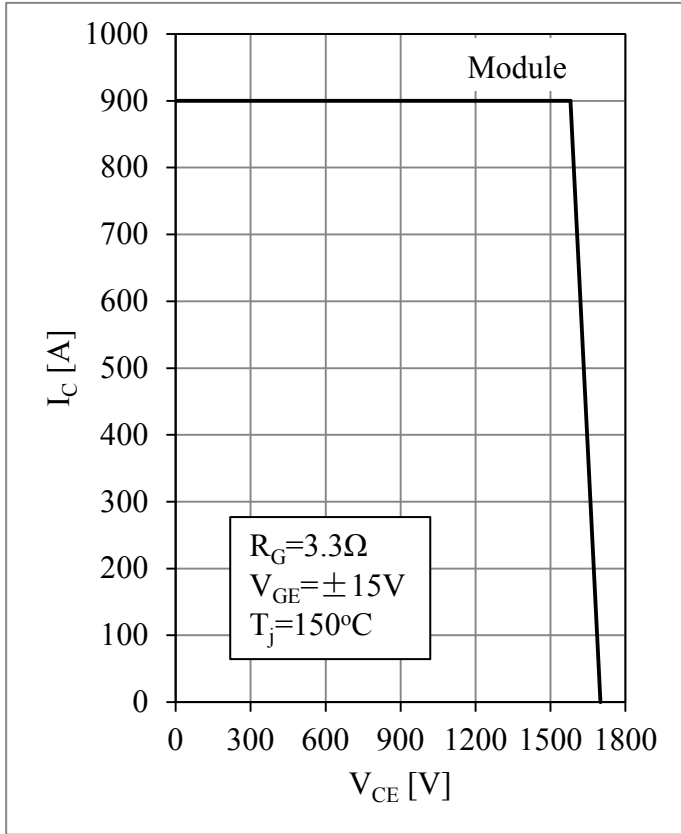


Fig 5. RBSOA

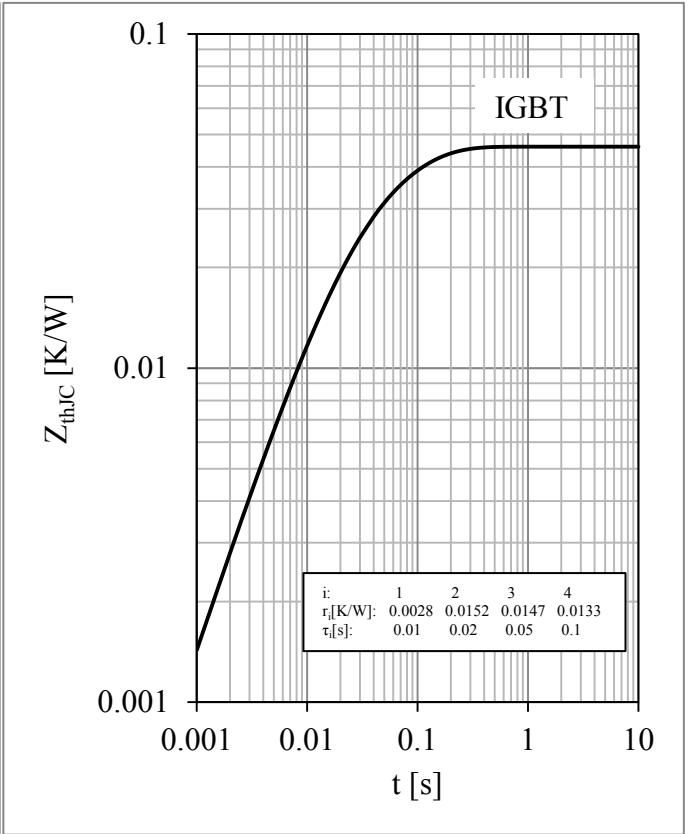


Fig 6. IGBT Transient Thermal Impedance

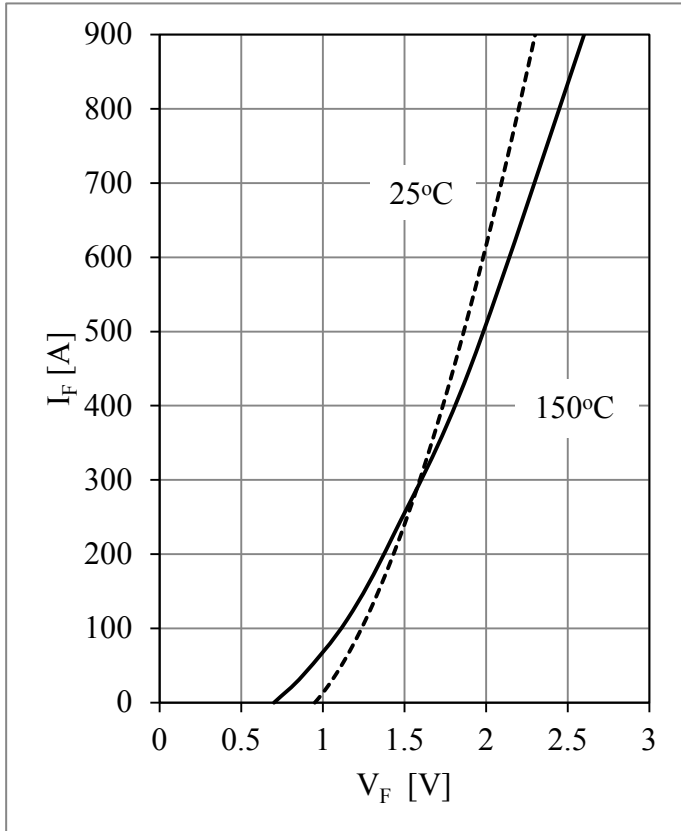


Fig 7. Diode Forward Characteristics

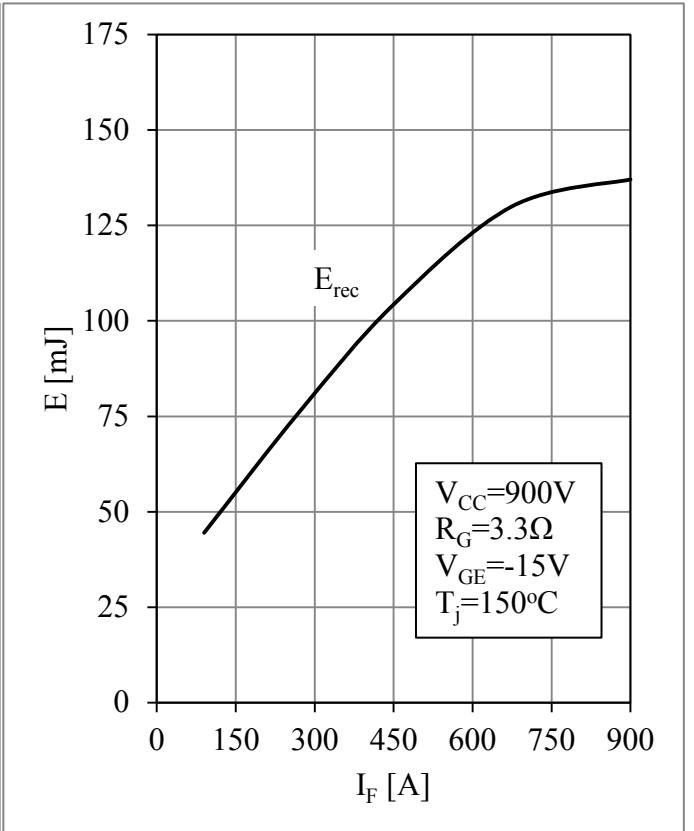


Fig 8. Diode Switching Loss vs. I_F

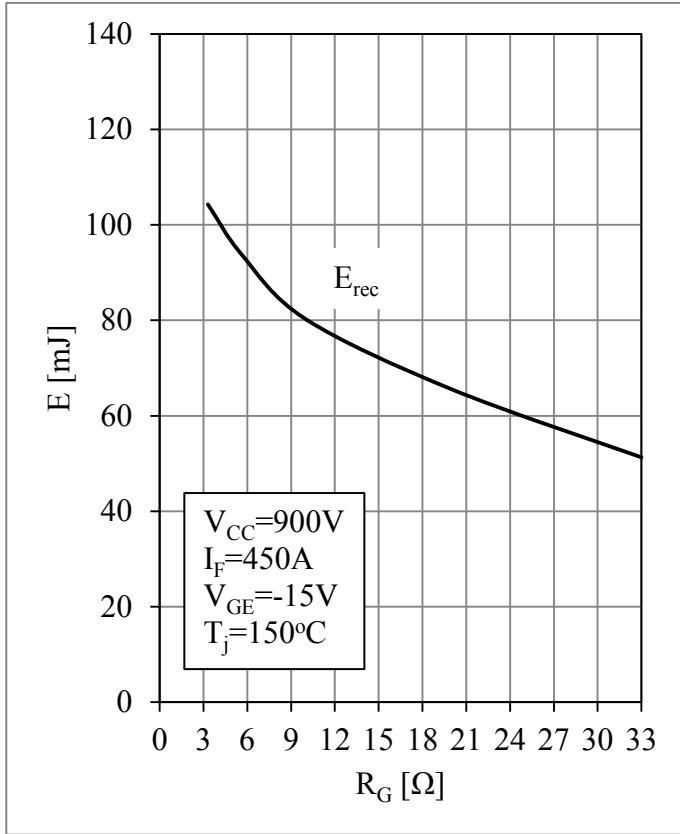


Fig 9. Diode Switching Loss vs. R_G

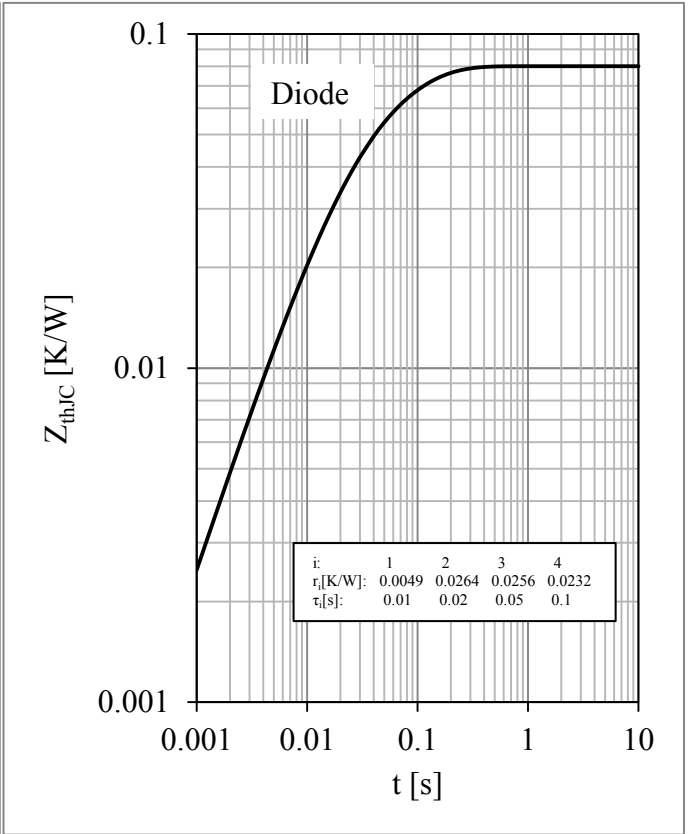


Fig 10. Diode Transient Thermal Impedance

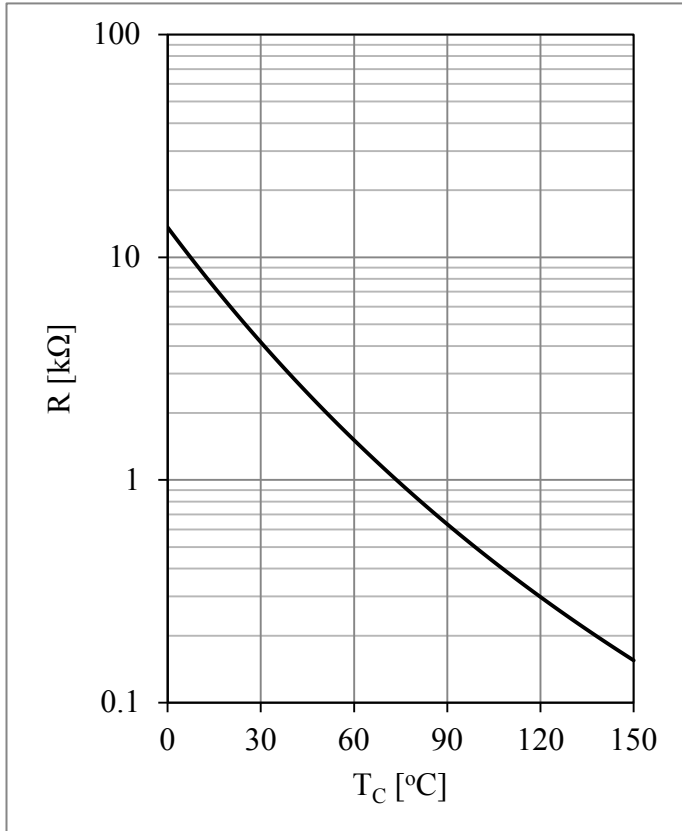


Fig 11. NTC Temperature Characteristic

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